

Erratum: Angle-resolved and core-level photoemission study of interfacing the topological insulator $\text{Bi}_{1.5}\text{Sb}_{0.5}\text{Te}_{1.7}\text{Se}_{1.3}$ with Ag, Nb, and Fe [Phys. Rev. B **92, 075127 (2015)]**

N. de Jong, E. Frantzeskakis, B. Zwartsenberg, Y. K. Huang, D. Wu, P. Hlawenka, J. Sánchez-Barriga, A. Varykhalov, E. van Heumen, and M. S. Golden

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In our paper an error was made in formulating the last sentence of the abstract that, unfortunately, was missed in the page proofs. The original closing sentence of the abstract is

For both Ag and Fe/Nb, these differing adsorption pathways still lead to the qualitatively similar and remarkable behavior for low temperature deposition that the chemical potential first moves downward (p-type dopant behavior) and then upward (n-type behavior) on increasing coverage.

Consistent with the experimental data (all figures remain unchanged) and the text in the main body and conclusions of the paper (all remain unchanged), this sentence should read

For both Ag and Fe/Nb, these differing adsorption pathways still lead to the qualitatively similar and remarkable behavior for low temperature deposition that the chemical potential first moves upward (n-type dopant behavior) and then downward (p-type behavior) on increasing coverage.

This correction simply brings the last sentence of the abstract in line with the body of the paper, and does not at all affect the data, arguments, or conclusions made in the original paper. Our apologies for the potential inconvenience caused to readers.